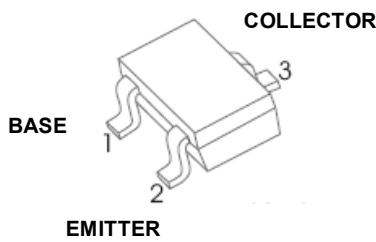


FEATURES

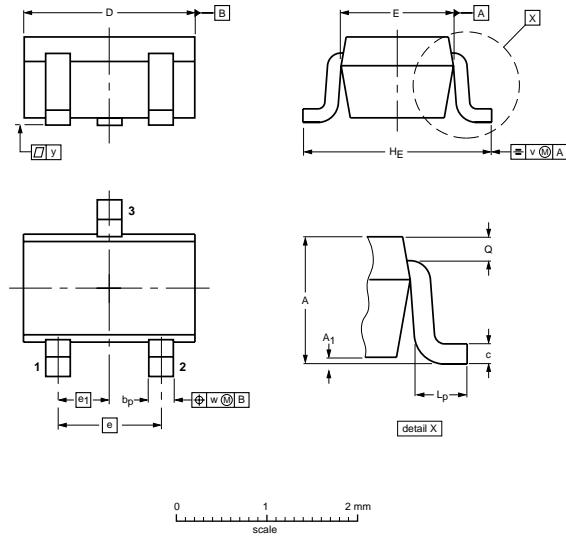
Complementary to MMBT5551W
 Small Surface Mount Package
 Ideal for Medium Power Amplification and Switching

MARKING: K4M



SOT - 323

SOT-323



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max	b _p	c	D	E	e	e ₁	H _E	L _p	Q	v	w
mm	1.1 0.8	0.1	0.4 0.3	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.23 0.13	0.2	0.2

MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CB0}	Collector-Base Voltage	-160	V
V _{CEO}	Collector-Emitter Voltage	-150	V
V _{EB0}	Emitter-Base Voltage	-5	V
I _c	Collector Current	-600	mA
P _c	Collector Power Dissipation	200	mW
R _{θJA}	Thermal Resistance From Junction To Ambient	625	°C/W
T _j	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55~+150	°C

MMST5401

ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-100\mu\text{A}, I_E=0$	-160			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1\text{mA}, I_B=0$	-150			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-10\mu\text{A}, I_C=0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB}=-120\text{V}, I_E=0$			-50	nA
Emitter cut-off current	I_{EBO}	$V_{EB}=-3\text{V}, I_C=0$			-50	nA
DC current gain	h_{FE}	$V_{CE}=-5\text{V}, I_C=-1\text{mA}$	80			
		$V_{CE}=-5\text{V}, I_C=-10\text{mA}$	100		300	
		$V_{CE}=-5\text{V}, I_C=-50\text{mA}$	50			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-50\text{mA}, I_B=-5\text{mA}$			-0.5	V
		$I_C=-10\text{mA}, I_B=-1\text{mA}$			-0.2	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=-50\text{mA}, I_B=-5\text{mA}$			-1	V
		$I_C=-10\text{mA}, I_B=-1\text{mA}$			-1	V
Transition frequency	f_T	$V_{CE}=-10\text{V}, I_C=-10\text{mA}, f=100\text{MHz}$	100			MHz
Collector output capacitance	C_{ob}	$V_{CB}=-10\text{V}, I_E=0, f=1\text{MHz}$			6	pF

RATING AND CHARACTERISTIC CURVES (MMST5401)

